

ABSTRACT OF THE DISCLOSURE

A method of forming a thin film transistor includes forming a gate electrode on a substrate, forming an organic layer over the substrate having the gate electrode, curing the organic layer in a first chamber, transferring the substrate having the organic layer from the first chamber to a second chamber without exposing the substrate having the organic layer to oxygen atmosphere during transfer, forming an active layer on the organic layer in the second chamber; and forming source and drain electrodes on the active layer.

5